TOSHIBA Transistor Silicon NPN Triple Diffused Type

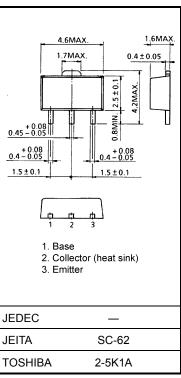
2SC5307

High Voltage Switching Applications

- High breakdown voltage: VCEO = 400 V
- Low saturation voltage: V_{CE} (sat) = 0.4 V (typ.) (I_C = 20 mA, I_B = 0.5 mA)

Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	400	V	
Collector-emitter voltage		V _{CEO}	400	V	
Emitter-base voltage		V _{EBO}	7	V	
Collector current	DC	Ι _C	50	mA	
	Pulse	I _{CP}	100		
Base current		Ι _Β	25	mA	
Collector power dissipation	Ta = 25°C		500	mW	
	Ta = 25°C	P _C	1000		
	(Note)		1000		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



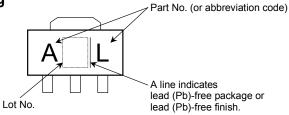
Weight: 0.05 g (typ.)

Note: Mounted on a ceramic substrate (250 $\text{mm}^2 \times 0.8 \text{ t}$)

Electrical Characteristics (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 400 V, I _E = 0	_	—	1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 7 V, I _C = 0	_	_	1	μA
Collector-emitter breakdown voltage	V _{CEO}	I _C = 1 mA, I _B = 0	400	—	—	V
DC current gain	h _{FE (1)}	V _{CE} = 5 V, I _C = 1 mA	80	—	—	
	h _{FE (2)}	V _{CE} = 5 V, I _C = 20 mA	100	_	300	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 20 mA, I _B = 0.5 mA	_	0.4	1.0	V
Base-emitter saturation voltage	V _{BE}	V _{CE} = 5 V, I _C = 20 mA	_	0.7	0.85	V
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	4.0	_	pF

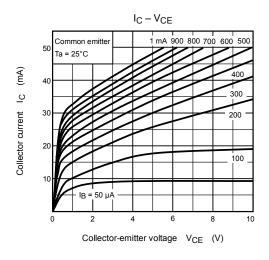
Marking

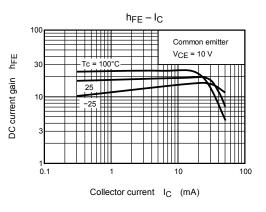


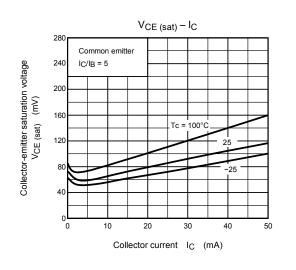
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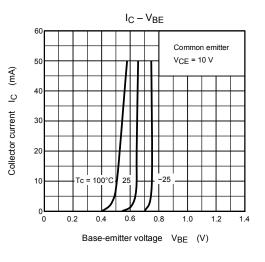
Unit: mm

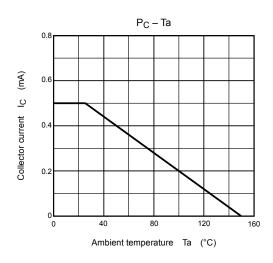
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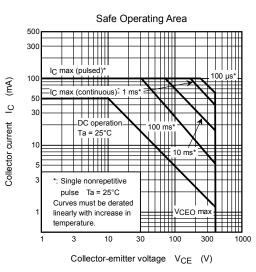












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